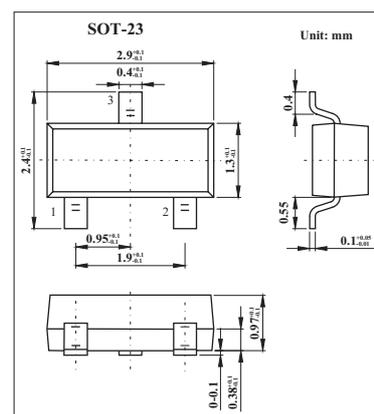


## Silicon PIN Diode

## BA886

## ■ Features

- Current-controlled RF resistor for switching and attenuating applications
- Frequency range above 1 M
- Designed for low IM distortion

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	50	V
Forward Current	$I_F$	50	mA
Operating temperature range	$T_{op}$	-55 to +125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Junction ambient	$R_{thJA}$	$\leq 450$	K/W

Note:

1. Package mounted on alumina  $15\text{ mm} \times 16.7\text{ mm} \times 0.7\text{ mm}$ .

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Forward Voltage	$V_F$	$I_F = 50\text{ mA}$			1.15	V	
Reverse Current	$I_R$	$V_R = 50\text{ V}$			50	nA	
Diode capacitance	$C_T$	$V_R = 50\text{ V}, f = 1\text{ MHz}$		0.23	0.35	pF	
		$V_R = 0\text{ V}, f = 100\text{ MHz}$		0.20			
Forward resistance	$r_f$	$f = 100\text{ MHz}$				$\Omega$	
		$I_F = 10\ \mu\text{ A}$		2400			
		$I_F = 1\text{ mA}$			58		
		$I_F = 10\text{ mA}$	6.5	7.8	10		
Zero bias conductance	$g_p$	$V_R = 0\text{ V}, f = 100\text{ MHz}$		40		$\mu\text{ S}$	
Series inductance	$L_s$			2		nH	

## ■ Marking

Marking	PC
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